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Vishay/Siliconix DG2517DN-T1-E4

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DG2517, DG2518

Vishay Siliconix

3- Ω , High Bandwidth, Dual SPDT Analog Switch

DESCRIPTION

The DG2517, DG2518 are low-voltage dual single-pole/double-throw monolithic CMOS analog switches. Designed to operate from 1.8 V to 5.5 V power supply, the DG2517, DG2518 achieves a bandwidth of 242 MHz while providing low on-resistance (3 Ω), excellent on-resistance matching (0.2 Ω) and flatness (1 Ω) over the entire signal range.

The DG2517, DG2518 offers the advantage of high linearity that reduces signal distortion, making ideal for audio, video, and USB signal routing applications. Additionally, the DG2517, DG2518 are 1.6 V logic compatible within the full operation voltage range.

Built on Vishay Siliconix's proprietary sub-micron high-density process, the DG2517, DG2518 brings low power consumption at the same time as reduces PCB spacing with the MSOP10 and DFN10 packages.

As a committed partner to the community and the environment, Vishay Siliconix manufactures this product with the lead (Pb)-free device terminations. The DFN package has a nickel-palladium-gold device termination and is represented by the lead (Pb)-free "-E4" suffix. The MSOP package uses 100 % matte Tin device termination and is represented by the lead (Pb)- free "-E3" suffix. Both the matte Tin and nickel-palladium-gold device terminations meet all JEDEC standards for reflow and MSL ratings.

FEATURES

- 1.8 V to 5.5 V single supply operation
- Low R_{ON} : 3 Ω at 4.2 V
- 242 MHz, 3 dB bandwidth
- Low off-isolation, 51 dB at 10 MHz
- + 1.6 V logic compatible

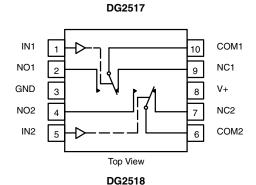
BENEFITS

- · High linearity
- · Low power consumption
- High bandwidth
- · Full rail signal swing range

APPLICATIONS

- · USB/UART signal switching
- · Audio/video switching
- Cellular phone
- Media players
- Modems
- Hard drives
- PCMCIA

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



IN1		COM1
NC1	2 9	NO1
GND	3 1/1 8	V+
NC2	4 7	NO2
IN2	5 6	COM2
	Top View	

TRUTH TABLE						
Logic	NC1 and NC2	NO1 and NO2				
0	ON	OFF				
1	OFF	ON				

ORDERING INFORMATION					
Temp. Range Package Part Number					
	MSOP-10	DG2517DQ-T1-E3			
- 40 °C to 85 °C	WISOF-10	DG2518DQ-T1-E3			
- 40 C t0 65 C	DFN-10	DG2517DN-T1-E4			
	DEN-10	DG2518DN-T1-E4			

Document Number: 74333 S-82589-Rev. B, 27-Oct-08



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DG2517, DG2518

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ABSOLUTE MAXIMUM RATINGS							
Parameter	Limit	Unit					
Reference to GND							
V+	- 0.3 to + 6	V					
IN, COM, NC, NO ^a	- 0.3 to (V+ + 0.3)	v					
Continuous Current (Any terminal)	± 50	mA					
Peak Current (Pulsed at 1 ms, 10 % duty	± 200	- IIIA					
Storage Temperature (D Suffix)	- 65 to 150	°C					
Power Dissipation (Packages) ^b	MSOP-10 ^c	320	mW				
Fower Dissipation (Fackages)	DFN-10 ^d	1191	11100				

- a. Signals on NC, NO, or COM or IN exceeding V+ will be clamped by internal diodes. Limit forward diode current to maximum current ratings. b. All leads welded or soldered to PC board. c. Derate 4.0 mW/°C above 70 °C. d. Derate 14.9 mW/°C above 70 °C.

		Test Conditions Otherwise Unless Specified			- 4	Limits 0 °C to 85		
Parameter	Symbol	$V+ = 3 V, \pm 10 \%, V_{IN} = 0$	5 or 1.4 V ^e	Temp.a	Min.b	Typ. ^c	Max.b	Unit
Analog Switch								
Analog Signal Range ^d	V_{NO}, V_{NC}, V_{COM}		Full	0		V+	٧	
On-Resistance	R _{ON}	V+ = 2.7 V, V _{COM} = I _{NO/NC} = 10 mA	1.5 V	Room Full		3.2	4.5 5.0	
R _{ON} Flatness	R _{ON} Flatness	$V+ = 2.7 \text{ V}, V_{COM} = 1$ $I_{NO/NC} = 10 \text{ m/s}$.5, 2 V	Room Full		1.0	1.4 16	Ω
R _{ON} Match Between Channels	ΔR _{ON}	V+ = 2.7 V, V _{COM} = I _{NO/NC} = 10 m/	1.5 V	Room Full		0.1	0.3 0.4	
Switch Off Leakage Current ^f	I _{NO(off),} I _{NC(off)}	V+ = 3.6 V, V _{NO} , V _{NC} = V _{COM} = 3 V/0.3	0.3 V/ 3 V	Room Full	- 1 - 10		1 10	
Switch On Leakage Current	I _{COM(off)}	V _{COM} = 3 V/0.3	V	Room Full	- 1 - 10		1 10	nA
Channel-On Leakage Current ^f	I _{COM(on)}	$V+ = 3.6 \text{ V}, V_{NO}, V_{NC} = V_{COM} = 0.3 \text{ V/3 V}$		Room Full	- 1 - 10		1 10	
Digital Control								•
Input High Voltage ^d	V _{INH}				1.4			V
Input Low Voltage	V _{INL}			Full			0.5	V
Input Capacitance	C _{in}			Full		4		pF
Input Current	I _{INL} or I _{INH}			Full	1		1	μΑ
Dynamic Characteristics								•
Turn-On Time	t _{ON}	V+ = 2.7 V, V _{NO} or V _{NO}	; = 1.5 V	Room Full		15	30 50	
Turn-Off Time	t _{OFF}	$R_L = 300 \ \Omega, \ C_L = 3$	5 pF	Room Full		10	25 35	ns
Break-Before-Make Time	t _d	V_{NO} or $V_{NC} = 1.5 \text{ V}$, $R_L = 300$		Full	1			
Charge Injection ^d	Q_{INJ}	$C_L = 1 \text{ nF, } V_{GEN} = 1.5 \text{ V, } F$	$R_{GEN} = 0 \Omega$	Room		1		рС
- 3 dB Bandwidth	BW	0 dBm, $C_L = 5$ pF, R_L	= 50 Ω	Room		242		MHz
Off-Isolation ^d	OIRR	$R_L = 50 \Omega, C_L = 5 pF$	f = 1 MHz	Room		- 71		dB
On-isolation			f = 10 MHz	Room		- 51		
Crosstalk ^d		B - 50 0 C - 5 - 5	f = 1 MHz	Room		- 73		dB
Ciossialk	X _{TALK}	$R_L = 50 \Omega, C_L = 5 pF$	f = 10 MHz	Room		- 55		
N. N. Off Conceitanced	C _{NO(off)}	V = 0 or V: f = 1 MHz		Room		8		
N _O , N _C Off Capacitance ^d	C _{NC(off)}			Room		8		pF
Channel On Conseitanced	C _{NO(on)}	- V _{IN} = 0 or V+, f = 1 MHz		Room		35		
Channel-On Capacitance ^d	C _{NC(on)}			Room		35		
Power Supply								
Power Supply Current	Power Supply Current I+ $V_{IN} = 0$ or V+ Full 0.01 1.0 μ					0.01	1.0	μΑ

Notes:
a. Room = 25 °C, Full = as determined by the operating suffix.
b. Typical values are for design aid only, not guaranteed nor subject to production testing.
c. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
d. Guarantee by design, nor subjected to production test.
e. V_{IN} = input voltage to perform proper function.
f. Guaranteed by 5 V leakage testing, not production tested.



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		Test Conditions Otherwise Unless Specified		Limits - 40 °C to 85 °C		°C		
Parameter	Symbol	$V+ = 5 V$, $\pm 10 \%$, $V_{IN} = 0.8 \text{ or } 2.0 V^e$	Temp.a	Min.b	Typ. ^c	Max.b	Unit	
Analog Switch						•		
Analog Signal Range ^d	V_{NO}, V_{NC}, V_{COM}		Full	0		V+	V	
On-Resistance	R _{ON}	V+ = 4.2 V, V _{COM} = 3.5 V, I _{NO/NC} = 10 mA	Room Full		3	4.0 4.3		
R _{ON} Flatness	R _{ON} Flatness	V+ = 4.2 V, V _{COM} = 1, 2, 3.5 V I _{NO/NC} = 10 mA	Room Full		1.1	1.4 1.6	Ω	
R _{ON} Match Between Channels	ΔR _{ON}	V+ = 4.2 V, V _{COM} = 3.5 V, I _{NO/NC} = 10 mA	Room Full		0.1	0.3 0.4		
Switch Off Leakage Current	I _{NO(off)} , I _{NC(off)}	V+ = 5.5 V	Room Full	- 1 - 10		1 10		
Switch On Leakage Current	I _{COM(off)}	V_{NO} , $V_{NC} = 1 \text{ V}/4.5 \text{ V}$, $V_{COM} = 4.5 \text{ V}/1 \text{ V}$	Room Full	- 1 - 10		1 10	nΑ	
Channel-On Leakage Current	I _{COM(on)}	$V+ = 5.5 \text{ V}, V_{COM} = V_{NO}, V_{NC} = 1 \text{ V}/4.5 \text{ V}$	Room Full	- 1 - 10		1 10		
Digital Control								
Input High Voltage ^d	V _{INH}		Full	2.0			V	
Input Low Voltage	V _{INL}		Full			0.8	1 V	
Input Capacitance	C _{in}		Full		4		рF	
Input Current	I _{INL} or I _{INH}	V _{IN} = 0 V or V+	Full	1		1	μA	
Dynamic Characteristics						•		
Turn-On Time	t _{ON}	V+ = 4.2 V, V _{NO} or V _{NC} = 3 V	Room Full		12	25 45		
Turn-Off Time	t _{OFF}	$R_L = 300 \Omega, C_L = 35 pF$	Room Full		8	20 30	ns	
Break-Before-Make Time	t _d	V_{NO} or V_{NC} = 3 V, R_L = 300 Ω , C_L = 35 pF	Full	1				
Charge Injection ^d	Q_{INJ}	$C_L = 1 \text{ nF, } V_{GEN} = 2.5 \text{ V, } R_{GEN} = 0 \Omega$	Room		2		рC	
- 3 dB Bandwidth	BW	0 dBm, $C_L = 5$ pF, $R_L = 50 \Omega$	Room		242		MH	
Off-Isolation ^d	OIRR	$R_L = 50 \Omega$, $C_L = 5 pF$ $f = 1 MHz$ f = 10 MHz	Room Room		- 71 - 51		alΓ	
Crosstalk ^d	X _{TALK}	$R_L = 50 \Omega$, $C_L = 5 pF$ $f = 1 MHz$ f = 10 MHz	Room Room		- 73 - 55		dE	
o o"o " d	C _{NO(off)}	·	Room		8		pF	
Source-Off Capacitance ^d	C _{NC(off)}	V _{IN} = 0 or V+, f = 1 MHz	Room		8			
A	C _{NO(on)}	$v_{IN} = 0 \text{ or } v+, i=1 \text{ in } mz$	Room		35			
Channel-On Capacitance ^d	C _{NC(on)}		Room		35		1	
Power Supply						<u> </u>		
Power Supply Range	V+			1.8		5.5	V	
Power Supply Current	l+	V _{IN} = 0 or V+	Full		0.01	1.0	μΔ	

Notes

- a. Room = 25 $^{\circ}$ C, Full = as determined by the operating suffix.
- b. Typical values are for design aid only, not guaranteed nor subject to production testing.
- c. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
- d. Guarantee by design, nor subjected to production test.
- e. V_{IN} = input voltage to perform proper function.
- f. Guaranteed by 5 V leakage testing, not production tested.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Document Number: 74333 www.vishay.com S-82589-Rev. B, 27-Oct-08 3

R_{ON} - On-Resistance (\Omega)

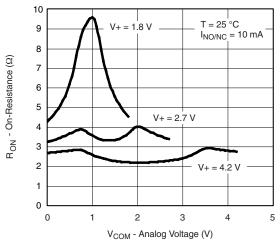


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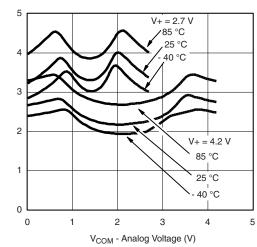
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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

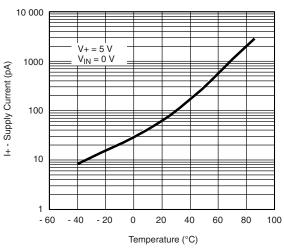




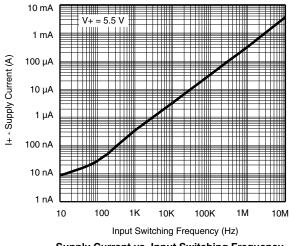
R_{ON} vs. V_{COM} and Supply Voltage



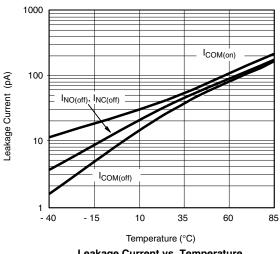
R_{ON} vs. Analog Voltage and Temperature



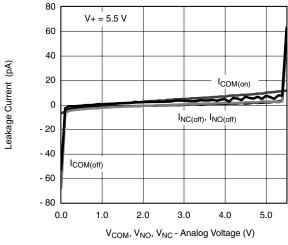
Supply Current vs. Temperature



Supply Current vs. Input Switching Frequency



Leakage Current vs. Temperature



Leakage vs. Analog Voltage

Loss (dB)

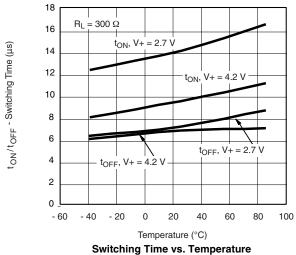


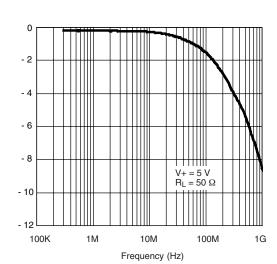


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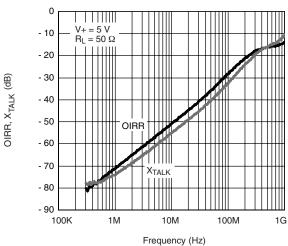
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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

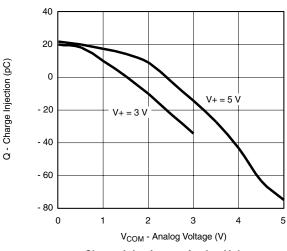




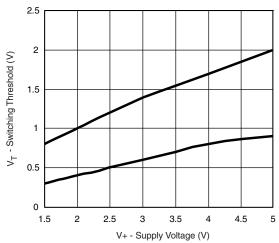
Insertion Loss vs. Frequency



Off-Isolation and Crosstalk vs. Frequency



Charge Injection vs. Analog Voltage



Switching Threshold vs. Supply Voltage

Document Number: 74333 S-82589-Rev. B, 27-Oct-08

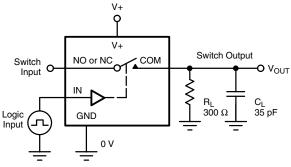


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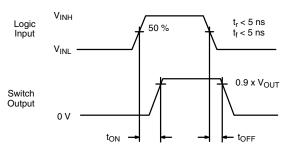
TEST CIRCUITS





 C_L (includes fixture and stray capacitance)

$$V_{OUT} = V_{COM} \left(\frac{R_L}{R_L + R_{ON}} \right)$$



Logic "1" = Switch On Logic input waveforms inverted for switches that have the opposite logic sense.

Figure 1. Switching Time

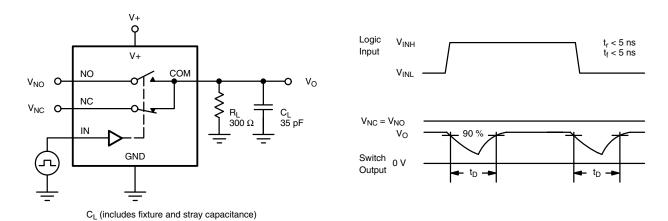


Figure 2. Break-Before-Make Interval

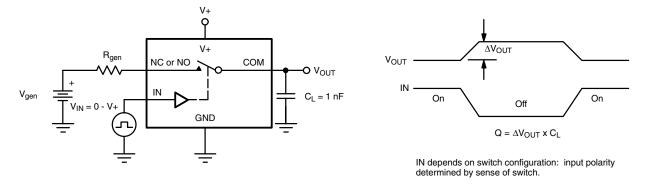


Figure 3. Charge Injection

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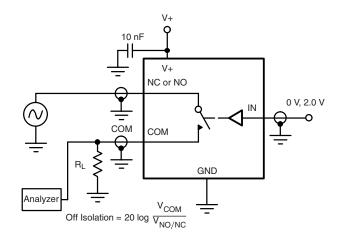
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TEST CIRCUITS



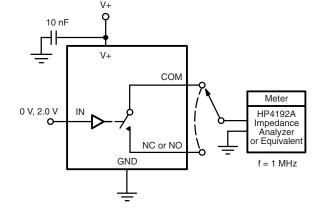


Figure 4. Off-Isolation

Figure 5. Channel Off/On Capacitance

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see http://www.vishay.com/ppg?74333.

Document Number: 74333 www.vishay.com S-82589-Rev. B, 27-Oct-08 7

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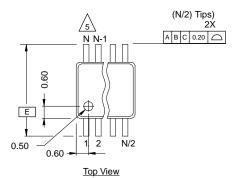
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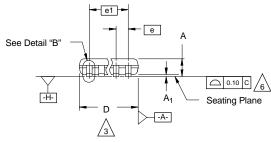


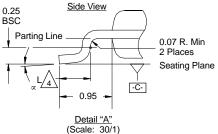
Package Information Vishay Siliconix

MSOP: 10-LEADS

JEDEC Part Number: MO-187, (Variation AA and BA)









- Die thickness allowable is 0.203 ± 0.0127 .
- Dimensioning and tolerances per ANSI.Y14.5M-1994.



Dimensions "D" and "E₁" do not include mold flash or protrusions, and are measured at Datum plane -H-, mold flash or protrusions shall not exceed



Dimension is the length of terminal for soldering to a substrate.



Terminal positions are shown for reference only.



Formed leads shall be planar with respect to one another within 0.10 mm at seating plane.



The lead width dimension does not include Dambar protrusion. Allowable Dambar protrusion shall be 0.08 mm total in excess of the lead width dimension at maximum material condition. Dambar cannot be located on the lower radius or the lead foot. Minimum space between protrusions and an adjacent lead to be 0.14 mm. See detail "B" and Section "C-C".



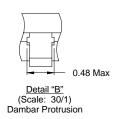
Section "C-C" to be determined at 0.10 mm to 0.25 mm from the lead tip.

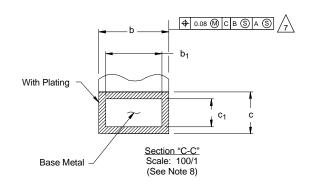
Controlling dimension: millimeters.

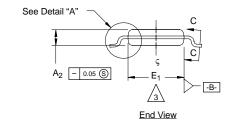
10. This part is compliant with JEDEC registration MO-187, variation AA and BA.

/11\ Datums -A- and -B- to be determined Datum plane -H-.

Exposed pad area in bottom side is the same as teh leadframe pad size.







N = 10L

	MI					
Dim	Min	Nom	Max	Note		
Α	1.10					
A ₁	0.05	0.10	0.15			
A ₂	0.75	0.85	0.95			
b	0.17	-	0.27	8		
b ₁	0.17	0.20	0.23	8		
С	0.13	-	0.23			
c ₁	0.13	0.15	0.18			
D		3.00 BSC		3		
Е		4.90 BSC				
E ₁	2.90	3.00	3.10	3		
е		0.50 BSC				
e ₁		2.00 BSC				
L	0.40	0.55	0.70	4		
N	10			5		
×	0°	4°	6°			
ECN: T-02080—Rev. C, 15-Jul-02 DWG: 5867						

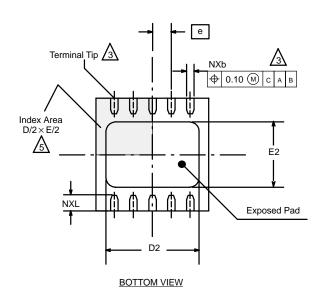
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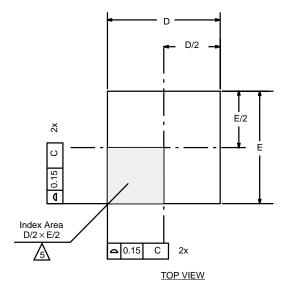


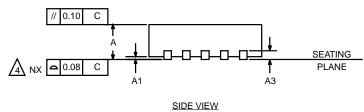


Package Information Vishay Siliconix

DFN-10 LEAD (3 X 3)







NOTES:

1. All dimensions are in millimeters and inches.

Dimension

N is the total number of terminals.

<u>√3\</u>

Dimension b applies to metallized terminal and is measured between 0.15 and 0.30 mm from terminal tip. $\,$



Coplanarity applies to the exposed heat sink slug as well as the terminal.



The pin #1 identifier may be either a mold or marked feature, it must be located within the zone iindicated.

	MI	LLIMETE	RS	INCHES			
Dim	Min	Nom	Max	Min	Nom	Max	
Α	0.80	0.90	1.00	0.031	0.035	0.039	
A1	0.00	0.02	0.05	0.000	0.001	0.002	
А3		0.20 BSC			0.008 BSC		
b	0.18	0.23	0.30	0.007 0.009 0.012			
D		3.00 BSC		0.118 BSC			
D2	2.20	2.38	2.48	0.087	0.094	0.098	
Е		3.00 BSC			0.118 BSC		
E2	1.49	1.64	1.74	0.059	0.065	0.069	
е		0.50 BSC	•		0.020 BSC	·	
L	0.30	0.40	0.50	0.012	0.016	0.020	
*Use millimeters as the primary measurement.							

ECN: S-42134—Rev. A, 29-Nov-04 DWG: 5943

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Revision: 13-Jun-16 1 Document Number: 91000